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PATENT

I hereby certify that on the date specified below, this correspondence is being deposited with the United States Postal Service as first-class mail in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Date January 12, 2007

Jennifer A. Steele
Jennifer A. Steele

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Wendell P. Noble

Attorney Docket No.: 500462.04

Patent No. : US 6,891,213 B1

Serial No. : 10/626,777

Issue Date : May 10, 2005

Filed : July 23, 2003

Title : BASE CURRENT REVERSAL SRAM MEMORY CELL AND METHOD

REQUEST FOR CERTIFICATE OF CORRECTION

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

**Certificate
JAN 23 2007
of Correction**

Sir:

A Certificate of Correction under 35 U.S.C. § 254 is respectfully requested for the above-identified patent in order to correct Patent and Trademark Office errors made during the printing of the patent. The changes in the patent needed to correct the errors are as follows:

<u>Column, Line</u>	<u>Reads</u>	<u>Should Read</u>
Item (56), Line 1	"A SRAM memory cell"	--An SRAM memory cell--
Item (56), Line 11	"and has a reduced power"	--and has reduced power--
Column 1, Line 42	"for 1.5V"	--for 1.8V--
Column 2, Lines 23 and 60	"a NPN"	--an NPN--
Column 2, Line 60	"in FIG. 2, however,"	--in FIG. 2; however,--
Column 2, Lines 62	"a NMOS"	--an NMOS--

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and 63

Column 3, Line 2	"340N"	--34 ON--
Column 4, Line 25	"SRAM"	--SRAM of--
Column 4, Line 53	"with in the"	--within the--
Column 5, Line 8	"concentration NA"	--concentration N_A --
Column 5, Line 10	"is a"	--is an--
Column 5, Line 12	"concentration ND"	--concentration N_D --
Column 5, Line 16	"concentration NA of about 102"	--concentration N_A of about 10^{20} --
Column 6, Line 40	"exposed portions the"	--exposed portions of the--
Column 7, Line 38	"n+ type"	--n+-type--
Column 7, Line 41	"F squared"	-- F^2 --
Column 8, Line 17	"SRAM 175 FIG. 11,"	--SRAM 175 of FIG. 11,--

The above errors for which correction is requested under 35 U.S.C. § 254 were made in the printing of the patent. The errors are considered sufficiently important to justify the processing of a Certificate of Correction under 35 U.S.C. § 254. A Form PTO-1050, in duplicate, is enclosed herewith.

The Commissioner is hereby authorized to charge payment of any fees associated with this communication to Deposit Account No. 50-1266. A duplicate copy of this sheet is enclosed.

JAN 23 2007

Favorable consideration of this Request is respectfully requested.

Respectfully submitted,

Date: Jan. 11, 2007

By: Edward W. Bulchis

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Enclosures:

Postcard

Form PTO-1050 (+ copy)

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UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : US 6,891,213 B1
DATED : May 10, 2005
INVENTOR(S) : Wendell P. Noble

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Column 5, Line 16	"concentration NA of about 10 ²⁰ "	--concentration N _A of about 10 ²⁰ --
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Column 8, Line 17	"SRAM 175 FIG. 11,"	--SRAM 175 of FIG. 11,--

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MAILING ADDRESS OF SENDER:

DORSEY & WHITNEY LLP
1420 Fifth Avenue, Suite 3400
Seattle, Washington 98101

Patent No. US 6,891,213 B1

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FORM PTO-1050 (REV. 3-82)

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